Vishay Semiconductors

Thyristor High Voltage Surface Mount Phase Control SCR, 10 A



TO-263AB (D²PAK)

PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	6.5 A							
V _{DRM} /V _{RRM}	800 V							
V _{TM}	< 1.15 V							
I _{GT}	15 mA							
TJ	-40 to +125 °C							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-10TTS08SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	2.5	3.5					
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A				
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5					

Note

• $T_A = 55 \ ^{\circ}C$, $T_J = 125 \ ^{\circ}C$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	6.5	A						
I _{RMS}		10	A						
V _{RRM} /V _{DRM}		800	V						
I _{TSM}		110	А						
V _T	6.5 A, T _J = 25 °C	1.15	V						
dV/dt		150	V/µs						
dl/dt		100	A/µs						
TJ	Range	-40 to +125	°C						

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-10TTS08SPbF	800	800	1.0

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RoHS COMPLIANT HALOGEN



VS-10TTS08SPbF Series



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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}	$I_{T(AV)}$ T _C = 112 °C, 180° conduction half sine wave		T 110 00 1000		6.5	
Maximum RMS on-state current	I _{T(RMS)}	$T_{\rm C} = 112$ C, 160 conduct	cion nan sine wave	10	А		
Maximum peak, one-cycle,		10 ms sine pulse, rated V_F	_{RRM} applied, T _J = 125 °C	95	A		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volta	age reapplied, T _J = 125 °C	110			
Maximum 12t fax fusing	l ² t	10 ms sine pulse, rated V_F	_{RRM} applied, T _J = 125 °C	45	A ² s		
Maximum I ² t for fusing	141	10 ms sine pulse, no volta	64	A-s			
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no vo	640	A²√s			
Maximum on-state voltage drop	V _{TM}	6.5 A, T _J = 25 °C	1.15	V			
On-state slope resistance	r _t	T 105 %O	17.3	mΩ			
Threshold voltage	V _{T(TO)}	T _J = 125 °C		0.85	V		
	1 /1	T _J = 25 °C		0.05			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM} / V_{DRM}$	1.0			
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T _J = 25 °C		30	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		50			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 $\%$		V/µs			
Maximum rate of rise of turned-on current	dl/dt			100	A∕µs		

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}		8.0	W			
Maximum average gate power	P _{G(AV)}		2.0	vv			
Maximum peak positive gate current	+I _{GM}		1.5	А			
Maximum peak negative gate voltage	-V _{GM}		10	V			
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	20				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15	mA			
		Anode supply = 6 V, resistive load, T_J = 125 °C	10				
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2				
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	1	v			
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	v			
Maximum DC gate voltage not to trigger	V _{GD}	T = 125 °C V = Poted volue	0.2				
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA			

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8					
Typical reverse recovery time	t _{rr}	T,1 = 125 °C	3	μs				
Typical turn-off time	t _q	1] = 123 0	100					

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THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	0/10				
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D ² PAK (SMD-220)	10TTS	08S				

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W

For recommended footprint and soldering techniques refer to application note #AN-994

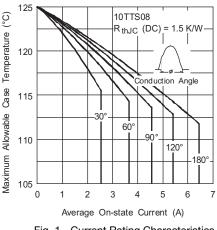
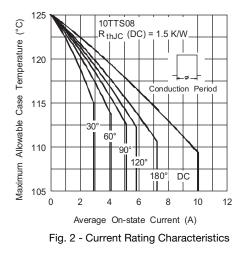


Fig. 1 - Current Rating Characteristics



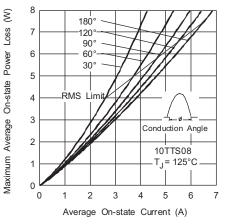


Fig. 3 - On-State Power Loss Characteristics

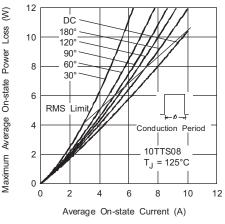


Fig. 4 - On-State Power Loss Characteristics

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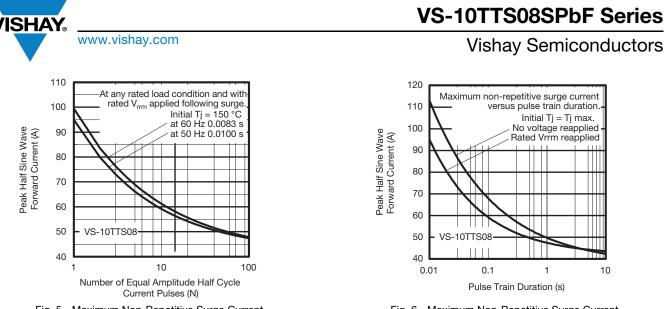
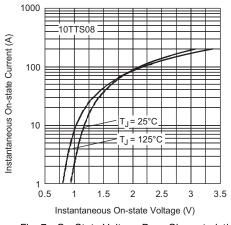


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current





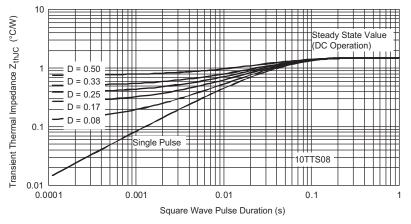


Fig. 8 - Thermal Impedance ZthJC Characteristics



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ORDERING INFORMATION TABLE

Device code	VS-	10	т	т	S	08	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 - Vishay Semiconductors product								
	2 - Current rating, RMS value								
	3 -	Circ	uit conf	iguratior	ו:				
		T =	single tl	nyristor					
	4 -	Pac	kage:						
		T =	TO-220	AC					
	5 -	Тур	e of silio	con:					
		S =	convert	er grade	Э				
	6 -	Volt	tage coo	le x 100	= V _{RRM}	1			
	7 -	S =	TO-220	D ² PAK	(SMD-	220) ve	rsion		
	8 -	Тар	Tape and reel option:						
		• TF	• TRL = tape and reel (left oriented)						
		• TF	• TRR = tape and reel (right oriented)						
	9 -	PbF	= lead	(Pb)-fre	е				

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-10TTS08SPbF	50	1000	Antistatic plastic tubes					
VS-10TTS08STRRPbF	800	800	13" diameter reel					
VS-10TTS08STRLPbF	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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